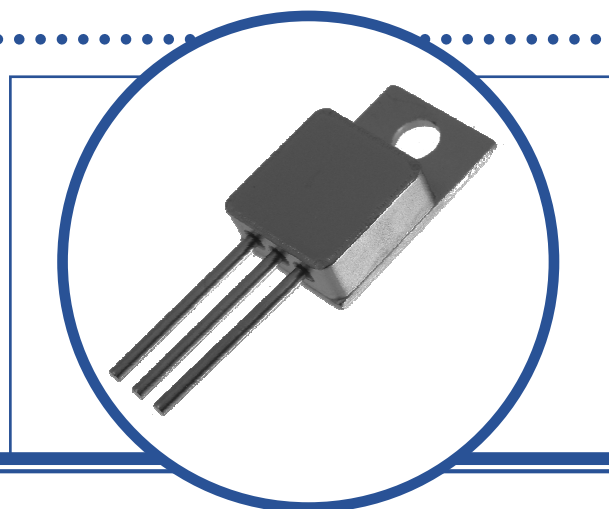


SILICON PLANAR EPITAXIAL PNP TRANSISTOR

BDS18

- High Voltage
- Hermetic TO220 Isolated Metal Package
- Ideally suited for Power Linear, Switching and general Purpose Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	-120V
V_{CEO}	Collector – Emitter Voltage	-120V
V_{EBO}	Emitter – Base Voltage	-5V
I_C	Continuous Collector Current	-8A
I_B	Base Current	-2A
P_D	Total Power Dissipation at $T_C \leq 75^\circ\text{C}$ Derate Above 75°C	50W 0.4W/ $^\circ\text{C}$
T_J	Junction Temperature Range	-65 to $+200^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65 to $+200^\circ\text{C}$

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case	2.5	$^\circ\text{C/W}$

** This datasheet supersedes document 3346

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

SILICON PLANAR EPITAXIAL PNP TRANSISTOR BDS18

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
$V_{(BR)CEO}^{(1)}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}$ $I_B = 0$	-120			V
I_{CEO}	Collector Cut-Off Current	$V_{CE} = -60\text{V}$ $I_B = 0$			-0.1	mA
I_{CBO}	Collector Cut-Off Current	$V_{CB} = -120\text{V}$ $I_E = 0$			-20	μA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = -5\text{V}$ $I_C = 0$			-10	
$h_{FE}^{(1)}$	Forward-current transfer ratio	$I_C = -0.5\text{A}$ $V_{CE} = -2\text{V}$	40		250	
		$I_C = -4\text{A}$ $V_{CE} = -2\text{V}$	15		150	
$V_{CE(sat)}^{(1)}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}$ $I_B = -0.05\text{A}$			-0.4	V
		$I_C = -4\text{A}$ $I_B = -0.4\text{A}$			-1.5	
$V_{BE(on)}^{(1)}$	Base-Emitter Voltage	$I_C = -1.0\text{A}$ $V_{CE} = -2\text{V}$			-1.4	

DYNAMIC CHARACTERISTICS

f_T	Transition Frequency	$I_C = -0.5\text{A}$ $V_{CE} = -4\text{V}$ $f = 5\text{MHz}$	10			MHz
t_{on}	Turn-On Time	$I_C = -2\text{A}$ $V_{CC} = -80\text{V}$ $I_{B1} = -0.2\text{A}$			0.5	μs
t_s	Storage Time	$I_C = -2\text{A}$ $V_{CC} = -80\text{V}$			1.5	
t_f	Fall Time	$I_{B1} = -I_{B2} = -0.2\text{A}$			0.3	

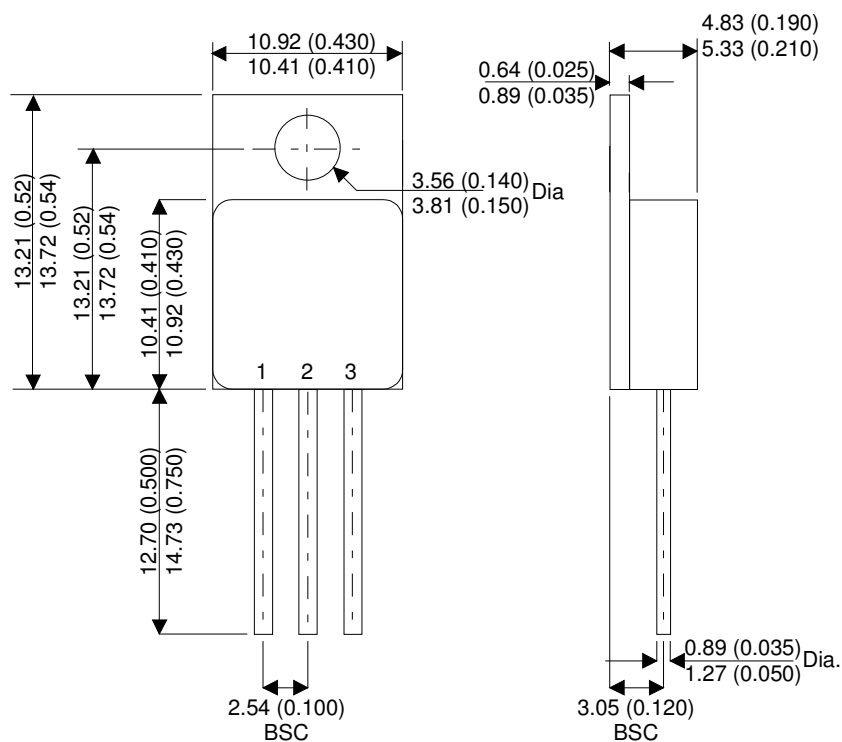
Notes

(1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$

SILICON PLANAR EPITAXIAL PNP TRANSISTOR BDS18

MECHANICAL DATA

Dimensions in mm (inches)



TO220M (TO-257AB)

Pin 1 - Base

Pin 2 - Collector

Pin 3 - Emitter